

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Hive application of:

John G. DeSteese and Larry C. Olsen

Application No. 10/727,062

Filed: December 2, 2003 Confirmation No. 4870

THERMOELECTRIC POWER SOURCE For:

UTILIZING AMBIENT ENERGY

HARVESTING FOR REMOTE SENSING

AND TRANSMITTING

Examiner: Alan D. Diamond

Art Unit: 1753

Attorney Reference No. 23-69853-01

CERTIFICATE OF MAILING

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Attorney or Agent for Applicant(s)

Date Mailed

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Listed on the accompanying form PTO-1449 and enclosed herewith are several Englishlanguage documents. Applicants respectfully request that these documents be listed as references cited on the issued patent.

Copies of United States patents and United States published patent applications do not have to be provided to the Patent Office (37 C.F.R. 1.98(a)(2)(ii)). Copies of unpublished U.S. applications do not have to be provided, as long as the application is available on PAIR, as this requirement of 37 C.F.R. § 1.98(a)(2)(iii) has been waived by the United States Patent and Trademark Office pursuant to the Official Gazette Notice on October 19, 2004 (1287 OG 163). Applicants will provide copies of such patents or applications upon request. Copies of the cited non-patent, non-application documents are enclosed.

Applicants filed this Information Disclosure Statement ("IDS") before the mailing date of a first Office action on the merits. As a result, no fee should be required to file this IDS. However, if the Patent Office determines that a fee is required for Applicants to file this IDS,

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The filing of this IDS shall not be construed to be an admission that the information cited in the statement is, or is considered to be, prior art or otherwise material to patentability as defined in 37 C.F.R. §1.56.

Respectfully submitted,

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ATION DISCLOSURE STATEMENT **BY APPLICANT** MAY 3 1 2005

Attorney Docket Number	23-69853-01
Application Number	10/727,062
Filing Date	December 2, 2003
First Named Inventor	John G. DeSteese
Art Unit	3744
Examiner Name	Not yet assigned

U.S. PATENT DOCUMENTS

& THADES Copies of U.S. Patent documents do not need to be provided, unless requested by the Patent and Trademark Office. For patents, provide the patent number and the issue date. For published U.S. applications, provide the publication number and the publication date. For unpublished pending patent applications, provide the application number and the filing date.

Examiner's Initials*	Cite No. (optional)	Number	Publication Date	Name of Applicant or Patentee
		6,096,964	8/2000	Ghamaty et al.
		6,096,965	8/2000	Ghamaty et al.
		6,288,321	9/2001	Fleurial et al.
		6,372,538	4/2002	Wendt et al.
		6,388,185	5/2002	Fleurial et al.
		6,413,645	7/2002	Graff et al.
	,			

FOREIGN PATENT DOCUMENTS

Examiner's Initials*	Cite No. (optional)	Country	Number	Publication Date	Name of Applicant or Patentee
Examiner's Initials*	Cite No. (optional)	OTHER DOCUMENTS			
					erator - self-sufficient energy n Thermoelectrics, pp. 575-577
	Stark, Ingo et al., "New Micro Thermoelectric Devices Based on Bismuth Telluride- Thin Solid Films," 18 th International Conference on Thermoelectrics, pp. 465-472 (1981)				

EXAMINER	DATE
SIGNATURE:	CONSIDERED:

^{*} Examiner: Initial if reference considered, whether or not in conformance with MPEP 609. Draw line through cite if not in conformance and not considered. Include copy of this form with next communication to applicant.

11/21/02).

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23-69853-01 Attorney Docket Number 10/727,062 **Application Number** Filing Date December 2, 2003 TION DISCLOSURE STATEMENT BY APPLICANT First Named Inventor John G. DeSteese Art Unit 3744 **Examiner Name** Not yet assigned Stölzer, M. et al., "Optimisation of p - (Bi_{0.25}Sb_{0.75})₂Te₃ and n - Bi₂(Te_{0.9}Se_{0.1})₃ Films for Thermoelectric Thin Film Components," 5 pages. Bergstresser, T.R. et al., "Copper on Polyimide Flexible Substrate for Ultra-Thin, High Performance Applications," 4 pages. Vining, Cronin B., "Semiconductors are cool," Nature, Vol. 413, pp. 577-578 (October 11, 2001). Venkatasubramanian, Rama et al., "Thin-film thermoelectric devices with high roomtemperature figures of merit," Nature, Vol. 413, pp. 597-602 (October 11 2001). Chen, G., "Thermal conductivity and ballistic-phonon transport in the cross-plane direction of superlattices," Phys. Rev. B, Vol. 57, No. 23, pp. 14958-14973 (June 15, 1998). Hicks, L.D. et al., "Effect of quantum-well structures on the thermoelectric figure of merit," Phys. Rev. B, Vol. 47, No. 19, pp. 12727-12731 (May 15, 1993). Kiely, J.H. et al., "Characteristics of Bi_{0.5}Sb_{1.5}Te₃/Be₂Te_{2.4}Se_{0.6} thin-film thermoelectric devices for power generation," Meas. Sci. Technol., Vol. 8, pp. 661-665 (June 1997). Nolas, G.S. et al., Thermoelectrics, "Basic Principles and New Materials Developments," Springer, Berline, pp. 111-146 (2001). Tritt, T., "Recent Trends in Thermoelectric Materials Research III," Academic Press, London, Vol. 7, pp. 50-55 (2001). Schaevitz, Samuel B. et al., "A Combustion-Based MEMS Thermoelectric Power Generator," The 11th International Conference on Solid-State Sensors and Actuators, Munich, Germany, 4 pages (June 10-14, 2001). 21st International Conference on Thermoelectrics, Jet Propulsion Laboratory, California Institute of Technology, Massachusetts Institute of Technology; "Texture formation in extruded rods of (Bi,SB)2(Te,Se)3 thermoelectric alloys," Vasilevskiy, E. et al. (August 26-29, 2002). Thin-film Superlattice Thermoelectric Technology, www.rti.org, 4 pages (2002). Physics of Thin Films: Sputter Deposition (Ohring: Chapter 3, sections 5-6), www.uccs.edu/~tchriste/courses/PHYS549/549lectures/sputter.html., 4 pages (Printed

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Physics of Thin Films: Sputter Deposition Techniques (Ohring: Chapter 3, section 7), www.uccs.edu/~tchriste/courses/PHYS549/549lectures/sputtertech.html., 5 pages (Printed

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	Venkatasubramanian, R., "Thin-film Superlattice Thermoelectric Devices for Power			
	Conversion and Cooling,"			
	www.its.org/its/ict2002/Abstracts/Rama Venkatasubramanian.htm (Printed 9/26/03).			
	D.T.S. GmbH: Thin Film Thermoelectric Generators, D.T.S., www.dts-			
	generator.com/index.htm (Printed 5/4/04).			
	D.T.S. GmbH: Thin Film Thermoelectric Generators, Low Power Thermoelectric			
	Generators; www.dts-generator.com/gen.txe.htm (Printed 5/4/04).			
•	D.T.S. GmbH: Thin Film Thermoelectric Generators, Infrared-Sensors, www.dts-			
	generator.com/sen-txe.htm (Printed 5/4/04).			
	D.T.S. GmbH: Thin Film Thermoelectric Generators, Research and development,			
	www.dts-generator.com/dev-txe.htm (Printed 5/4/04).			

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